

What is claimed is:

1. A semiconductor device comprising:
a substrate which has a main surface; and
an alignment mark which is formed on the main surface and which has a pattern, wherein the pattern in a plane view has a shape that is obtained by eliminating corners from a polygon.
2. The semiconductor device as claimed in claim 1, wherein the polygon is a rectangle.
3. The semiconductor device as claimed in claim 1, wherein the width of the pattern of the alignment mark ranges from 0.6 μm to 0.8 μm .
4. The semiconductor device as claimed in claim 1, wherein the pattern of the alignment mark comprises a metal film.
5. The semiconductor device as claimed in claim 4, further comprising a cover film that is formed over the metal film to prevent the oxidation of the metal film.
6. The semiconductor device as claimed in claim 5, wherein a pattern of the cover film in a plane view has a shape that is obtained by eliminating corners from the polygon.
7. The semiconductor device as claimed in claim 5, wherein the width of the pattern of the cover film is 1 μm to several μm wider in one side than the width of the pattern formed of the metal film.

8. The semiconductor device as claimed in claim 5, wherein the cover film is formed of iridium-based metal.

9. A semiconductor device comprising:

a substrate which has a main surface; and

an alignment mark which is formed on the main surface and which has first through fourth sub patterns,

wherein the first and second sub patterns are arranged so as to oppose each other and the third and forth sub patterns are arranged so as to oppose each other and wherein the first through fourth sub patterns are separated from one another.

10. The semiconductor device as claimed in claim 9, wherein the width of the sub patterns of the alignment mark ranges from 0.6 μm to 0.8 μm .

11. The semiconductor device as claimed in claim 9, wherein the alignment mark comprises a metal film.

12. The semiconductor device as claimed in claim 11, further comprising a cover film that is formed over the metal film to prevent the oxidation of the metal film.

13. The semiconductor device as claimed in claim 12, wherein the cover film has first through fourth patterns and wherein the first through fourth patterns are formed on the first through fourth sub patterns, respectively.

14. The semiconductor device as claimed in claim 13, wherein the width of the first through fourth patterns are 1 μm to several μm wider in one side than the width of the

corresponding first through fourth sub patterns.

15. The semiconductor device as claimed in claim 12, wherein the cover film is formed of iridium-based metal.